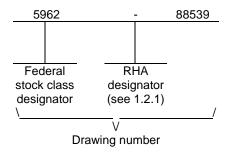
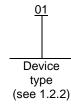
							F	REVISI	ONS										
LTR				[DESCR	RIPTIO	N					DATE (YR-MO-DA)			APPROVED				
А	Add case outline 2. Add input voltage test. Add footnote <u>3</u> /. Editorial changes throughout.							90-03-30		M. POELKING		3							
В	Change	e boiler	plate to ad	d one-p		numbe	ers.						97-1	2-08			R. MO	NINNC	
С	Add ra	diation	for delta lim hardened a	assuran	ce requ								99-0	3-01			R. M	NINNC	
D			erence to MIL-STD-973 with reference to MIL-P			PRF-38	535.			04-0	8-06			R. M	NINNC				
Е	Add a i	new foo	otnote unde	o reflect current requirements gt e under paragraph 1.5 and Table I ro								05-0	8-09			R. M	NINNC		
F	Update unused	e drawir d group	awing to reflect current requirements. Changes to pup E boilerplate paragraphsrrp				1.5. C	eleted			11-0	2-16			C. SAFFLE				
THE ORIGINA	L FIRST S	SHEET	OF THIS C	PRAWIN	IG HAS	BEEN	I REPL	ACED.											
REV SHEET	AL FIRST S	SHEET	OF THIS C	PRAWIN	IG HAS	BEEN	I REPL	ACED.											
REV SHEET REV	L FIRST S	SHEET	OF THIS C	PRAWIN	IG HAS	SBEEN	I REPL	ACED.											
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REV SHEET REV SHEET REV STATUS		SHEET	RE	V	IG HAS	F	F	F	F	F	F	F	F	F	F	F	F	F	
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REV SHEET REV SHEET REV STATUS OF SHEETS PMIC N/A	6		RE SH PRE	V EET EPARED	D BY	F 1	F	F	F		6	7 DLA I	-AND BUS,	9 AND OHIO	10 MAF O 432	11 RITIM 218-3	12 E	-	
REV SHEET REV SHEET REV STATUS OF SHEETS PMIC N/A		D	RE SH PRE CHE	V EET EPAREE OSEPH ECKED D. A. DiO	D BY H A. KE BY CENZO	F 1	F	F	F		6	7 DLA I	-AND BUS,	9 AND OHIO	10 MAF	11 RITIM 218-3	12 E	-	
REV SHEET REV SHEET REV STATUS OF SHEETS PMIC N/A STA MICRO DR/	INDARI OCIRCI AWING	D UIT 6	RE SH PRE CHE	V EET OSEPH ECKED D. A. DIO PROVED	D BY H A. KE BY CENZO D BY L A. FF	F 1 RBY	F 2	F	F 4	5 SROC	CCC	7 DLA I DLUM http	AND BUS, o://ww	9 AND OHIO	D MAF D 432 cc.dl	RITIM 218-3: a.mil	12 E 990	13	
REV SHEET REV SHEET REV STATUS OF SHEETS PMIC N/A STA MICRO DR.	INDARI OCIRCU AWING ING IS AV, JSE BY AL ARTMENTS	D UIT 6	RE SH PRE CHE	V EET OSEPH ECKED). A. DiG	D BY H A. KE BY CENZO D BY L A. FF	F 1 RBY	F 2	F	F 4	5 CROC RDEI	6	7 DLA I DLUM http	AND BUS, 0://ww	9 AND OHIO OHIO OHIO OHIO OHIO OHIO OHIO OHI	D MAF D 432 CC.dl	RITIM 218-3: a.mil	12 E 990	13	
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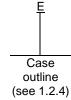
1. SCOPE

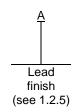
- 1.1 <u>Scope</u>. This drawing documents two product assurance class levels consisting of high reliability (device classes Q and M) and space application (device class V). A choice of case outlines and lead finishes are available and are reflected in the Part or Identifying Number (PIN). When available, a choice of Radiation Hardness Assurance (RHA) levels is reflected in the PIN.
 - 1.2 PIN. The PIN is as shown in the following examples.

For device classes M and Q:

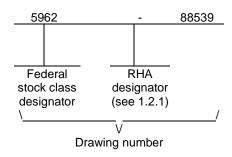


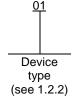


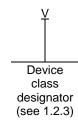


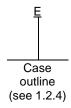


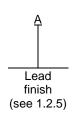
For device class V:











- 1.2.1 RHA designator. Device classes Q and V RHA marked devices meet the MIL-PRF-38535 specified RHA levels and are marked with the appropriate RHA designator. Device class M RHA marked devices meet the MIL-PRF-38535, appendix A specified RHA levels and are marked with the appropriate RHA designator. A dash (-) indicates a non-RHA device.
 - 1.2.2 <u>Device type(s)</u>. The device type(s) identify the circuit function as follows:

Device type	Generic number	Circuit function		
01	AD524	Precision instrumentation amplifier		

1.2.3 <u>Device class designator</u>. The device class designator is a single letter identifying the product assurance level as listed below. Since the device class designator has been added after the original issuance of this drawing, device classes M and Q designators will not be included in the PIN and will not be marked on the device.

Device class

Device requirements documentation

M Vendor self-certification to the requirements for MIL-STD-883 compliant, non-JAN class level B microcircuits in accordance with MIL-PRF-38535, appendix A

Q or V Certification and qualification to MIL-PRF-38535

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1.2.4 <u>Case outlines</u>. The case outlines are as designated in MIL-STD-1835 and as follows:

Outline letter	Descriptive designator	<u>Terminals</u>	Package style
E	GDIP1-T16 or CDIP2-T16	16	Dual-in-line
2	CQCC1-N20	20	Square leadless chip carrier

1.2.5 <u>Lead finish</u>. The lead finish is as specified in MIL-PRF-38535 for device classes Q and V or MIL-PRF-38535, appendix A for device class M.

1.3 Absolute maximum ratings. 1/

Supply voltage (V _S)	±18 V dc
Internal power dissipation (PD)	280 mW
Input voltage	±V _S maximum
Storage temperature range (T _{STG})	-65°C to +150°C
Lead temperature (soldering, 10 seconds)	+300°C
Thermal resistance, junction-to-case (θ JC)	See MIL-STD-1835
Thermal resistance, junction-to-ambient (θ_{JA}) :	
Case outline E Case outline 2	

1.4 Recommended operating conditions.

Supply voltage (V _S)	±6 V dc to ±18 V dc
Ambient operating temperature range (T _A)	-55°C to +125°C

1.5 Radiation features.

Maximum total dose available (dose rate = 50 - 300 rads(Si)/s) 100 Krads(Si) 2/

2. APPLICABLE DOCUMENTS

2.1 <u>Government specification, standards, and handbooks</u>. The following specification, standards, and handbooks form a part of this drawing to the extent specified herein. Unless otherwise specified, the issues of these documents are those cited in the solicitation or contract.

DEPARTMENT OF DEFENSE SPECIFICATION

MIL-PRF-38535 - Integrated Circuits, Manufacturing, General Specification for.

DEPARTMENT OF DEFENSE STANDARDS

MIL-STD-883 - Test Method Standard Microcircuits.

MIL-STD-1835 - Interface Standard Electronic Component Case Outlines.

^{2/} These parts may be dose rate sensitive in a space environment and may demonstrate enhanced low dose rate effects. Radiation end point limits for the noted parameters are guaranteed only for the conditions as specified in MIL-STD-883, method 1019, condition A.

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^{1/} Stresses above the absolute maximum rating may cause permanent damage to the device. Extended operation at the maximum levels may degrade performance and affect reliability.

DEPARTMENT OF DEFENSE HANDBOOKS

MIL-HDBK-103 - List of Standard Microcircuit Drawings.

MIL-HDBK-780 - Standard Microcircuit Drawings.

(Copies of these documents are available online at https://assist.daps.dla.mil/quicksearch/ or from the Standardization Document Order Desk, 700 Robbins Avenue, Building 4D, Philadelphia, PA 19111-5094.)

2.2 <u>Order of precedence</u>. In the event of a conflict between the text of this drawing and the references cited herein, the text of this drawing takes precedence. Nothing in this document, however, supersedes applicable laws and regulations unless a specific exemption has been obtained.

3. REQUIREMENTS

- 3.1 <u>Item requirements</u>. The individual item requirements for device classes Q and V shall be in accordance with MIL-PRF-38535 and as specified herein or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not affect the form, fit, or function as described herein. The individual item requirements for device class M shall be in accordance with MIL-PRF-38535, appendix A for non-JAN class level B devices and as specified herein.
- 3.2 <u>Design, construction, and physical dimensions</u>. The design, construction, and physical dimensions shall be as specified in MIL-PRF-38535 and herein for device classes Q and V or MIL-PRF-38535, appendix A and herein for device class M.
 - 3.2.1 Case outlines. The case outlines shall be in accordance with 1.2.4 herein .
 - 3.2.2 Terminal connections. The terminal connections shall be as specified on figure 1.
 - 3.2.3 <u>Block diagram</u>. The block diagram shall be as specified on figure 2.
 - 3.2.4 Radiation exposure circuit. The radiation exposure circuit shall be as specified on figure 3.
- 3.3 <u>Electrical performance characteristics and postirradiation parameter limits</u>. Unless otherwise specified herein, the electrical performance characteristics and postirradiation parameter limits are as specified in table I and shall apply over the full ambient operating temperature range.
- 3.4 <u>Electrical test requirements</u>. The electrical test requirements shall be the subgroups specified in table IIA. The electrical tests for each subgroup are defined in table I.
- 3.5 <u>Marking</u>. The part shall be marked with the PIN listed in 1.2 herein. In addition, the manufacturer's PIN may also be marked. For packages where marking of the entire SMD PIN number is not feasible due to space limitations, the manufacturer has the option of not marking the "5962-" on the device. For RHA product using this option, the RHA designator shall still be marked. Marking for device classes Q and V shall be in accordance with MIL-PRF-38535. Marking for device class M shall be in accordance with MIL-PRF-38535, appendix A.
- 3.5.1 <u>Certification/compliance mark</u>. The certification mark for device classes Q and V shall be a "QML" or "Q" as required in MIL-PRF-38535. The compliance mark for device class M shall be a "C" as required in MIL-PRF-38535, appendix A.
- 3.6 <u>Certificate of compliance</u>. For device classes Q and V, a certificate of compliance shall be required from a QML-38535 listed manufacturer in order to supply to the requirements of this drawing (see 6.6.1 herein). For device class M, a certificate of compliance shall be required from a manufacturer in order to be listed as an approved source of supply in MIL-HDBK-103 (see 6.6.2 herein). The certificate of compliance submitted to DLA Land and Maritime-VA prior to listing as an approved source of supply for this drawing shall affirm that the manufacturer's product meets, for device classes Q and V, the requirements of MIL-PRF-38535 and herein or for device class M, the requirements of MIL-PRF-38535, appendix A and herein.
- 3.7 <u>Certificate of conformance</u>. A certificate of conformance as required for device classes Q and V in MIL-PRF-38535 or for device class M in MIL-PRF-38535, appendix A shall be provided with each lot of microcircuits delivered to this drawing.
- 3.8 <u>Notification of change for device class M.</u> For device class M, notification to DLA Land and Maritime-VA of change of product (see 6.2 herein) involving devices acquired to this drawing is required for any change that affects this drawing.

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		TABLE I. Elec	ctrical performand	ce characteristic	CS.				
Test	Symbol	ol Conditions $\underline{1}/\underline{2}/$ -55°C \leq T _A \leq +125°C unless otherwise specified		-55°C ≤ T _A ≤ +125°C Group A Device		Device type	Lim	iits	Unit
				· .	,,	Min	Max		
Gain error 1	GE ₁	G = 1, V _O =	±10 V	1	01		±.05	%	
			M, D, P, L, R				.05		
Gain error 10	GE ₁₀	G = 10, V _O	= ±10 V	1	01		±.25	%	
			M, D, P, L, R				.25		
Gain error 100	GE ₁₀₀	G = 100, V _C) = ±10 V	1	01		±.5	%	
			M, D, P, L, R				.5		
Gain error 1000	GE ₁₀₀₀	G = 1000, V	O = ±10 V	1	01		±2.0	%	
			M, D, P, L, R				2.0		
Gain error drift 1	TCGE ₁	G = 1, V _O =	±10 V <u>3</u> /	2, 3	01		±5	ppm/°C	
Gain error drift 10	TCGE ₁₀	G = 10, V _O =	= ±10 V <u>3</u> /	2, 3	01		±10	ppm/°C	
Gain error drift 100	TCGE ₁₀₀	G = 100, V _C) = ±10 V <u>3</u> /	2, 3	01		±25	ppm/°C	
Gain error drift 1000	TCGE ₁₀₀₀	G = 1000, V	′ _O = ±10 V <u>3</u> /	2, 3	01		±50	ppm/°C	
Input offset voltage	Vosi	V _{IN} = 0 V, T	A = 25°C	1	01		±100	μV	
			M, D, P, L, R				1.0	mV	
Input offset voltage drift	TCV _{OSI}	V _{IN} = 0 V, G	G = 1000 <u>3</u> /	2, 3	01		<u>±2</u>	μV/°C	
Output offset voltage	Voso	V _{IN} = 0 V, T	A = 25°C	1	01		±3	mV	
			M, D, P, L, R				25		
Output offset voltage drift	TCV _{OSO}	V _{IN} = 0 V, G	S = 1 <u>3</u> /	2, 3	01		±50	μV/°C	
Input bias current	IB	G = 1		1	01	-50	50	nA	
				2, 3		-70	70		
			M, D, P, L, R	1			1000		
Input offset current	I _{IO}	I _{IO} = (I _{B+}) -	(I _{B-})	1	01	-35	35	nA	
		G = 1		2, 3		-50	50		
			M, D, P, L, R	1			100		

See footnotes at end of table.

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TABLE I. <u>Electrical performance characteristics</u> - Continued.

Test	Symbol		ons $1/2/$ $A \le +125^{\circ}C$ vise specified	Group A subgroups	Device type	Lim	nits	Unit
			·		3,50	Min	Max	
Common mode rejection	CMRR1	G = 1 V _{IN} = 0 V to +	<u>3</u> / ⊦10 V	1, 2, 3	01	70		dB
Common mode rejection	-CMRR1	G = 1 V _{IN} = 0 V to -	<u>3</u> /	1, 2, 3	01	70		dB
Common mode rejection	CMRR10	G = 10 V _{IN} = 0 V to +	<u>3</u> / ⊦10 V	1, 2, 3	01	90		dB
Common mode rejection	-CMRR10	G = 10 V _{IN} = 0 V to -	<u>3</u> / 10 V	1, 2, 3	01	90		dB
Common mode rejection	CMRR100	G = 100 V _{IN} = 0 V to +	<u>3</u> / ⊦10 V	1, 2, 3	01	100		dB
Common mode rejection	-CMRR100	G = 100 V _{IN} = 0 V to -	<u>3</u> / 10 V	1, 2, 3	01	100		dB
Common mode rejection	CMRR1000	G = 1000 V _{IN} = 0 V to +	<u>3</u> / ⊦10 V	1, 2, 3	01	110		dB
Common mode rejection	-CMRR1000	G = 1000 V _{IN} = 0 V to -	<u>3</u> / 10 V	1, 2, 3	01	110		dB
Power supply current	Icc	G = 1		1, 2, 3	01		5	mA
			M, D, P, L, R	1			5	
Power supply rejection	PSRR1	G = 1	<u>3</u> / <u>4</u> /	1, 2, 3	01	75		dB
Power supply rejection	PSRR10	G = 10	<u>3</u> / <u>4</u> /	1, 2, 3	01	95		dB
Power supply rejection	PSRR100	G = 100	<u>3</u> / <u>4</u> /	1, 2, 3	01	105		dB
Power supply rejection	PSRR1000	G = 1000	<u>3</u> / <u>4</u> /	1, 2, 3	01	115		dB

See footnotes at end of table.

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TABLE I. Electrical performance characteristics - Continued.

Test	Symbol		Group A subgroups	Device type	Limits		Unit
					Min	Max	
Input voltage	VIN	Differential, linear, <u>3</u> / G = 1, T _A = 25°C	1	01	±10		V
		Common mode, linear 3/ G = 1, T _A = 25°C			± 7		
		Differential, safe, T _A = 25°C <u>3</u> / <u>5</u> / <u>6</u> /				± 36	
		Common, safe, T _A = 25°C <u>3/ 5/ 6/</u>				± 36	

- 1/ Devices supplied to this drawing have been characterized through all levels M, D, P, L, R of irradiation. However, this device is only tested at the "R" level. Pre and Post irradiation values are identical unless otherwise specified in table I. $V_S = \pm 15 \text{ V}$, $R_L = 2 \text{ k}\Omega$, unless otherwise specified.
- 2/ These parts may be dose rate sensitive in a space environment and may demonstrate enhanced low dose rate effects. Radiation end point limits for the noted parameters are guaranteed only for the conditions as specified in MIL-STD-883, method 1019, condition A.
- 3/ This parameter not tested post radiation.
- <u>4/</u> Power supply voltage tested at ± 15 V with a swing to ± 12 V.
- 5/ Input voltage (differential, safe) is the maximum voltage difference that can exist between the two input pins without damage to the device. Input voltage (common mode, safe) is the maximum voltage that can be applied to both input pins at the same time without damage to the device. The addition of the differential and common mode voltages shall not exceed ±36 volts and can be applied when the device power is on or off without damage to the device.
- 6/ Guaranteed if not tested to the limits specified.
- 3.9 <u>Verification and review for device class M.</u> For device class M, DLA Land and Maritime, DLA Land and Maritime 's agent, and the acquiring activity retain the option to review the manufacturer's facility and applicable required documentation. Offshore documentation shall be made available onshore at the option of the reviewer.
- 3.10 <u>Microcircuit group assignment for device class M.</u> Device class M devices covered by this drawing shall be in microcircuit group number 49 (see MIL-PRF-38535, appendix A).

4. VERIFICATION

- 4.1 <u>Sampling and inspection</u>. For device classes Q and V, sampling and inspection procedures shall be in accordance with MIL-PRF-38535 or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not affect the form, fit, or function as described herein. For device class M, sampling and inspection procedures shall be in accordance with MIL-PRF-38535, appendix A.
- 4.2 <u>Screening</u>. For device classes Q and V, screening shall be in accordance with MIL-PRF-38535, and shall be conducted on all devices prior to qualification and technology conformance inspection. For device class M, screening shall be in accordance with method 5004 of MIL-STD-883, and shall be conducted on all devices prior to quality conformance inspection.

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Device type	01		
Case outlines	E	2	
Terminal number	Termina	l symbol	
1	-INPUT	NC	
2	+INPUT	-INPUT	
3	RG ₂	+INPUT	
4	INPUT NULL	RG ₂	
5	INPUT NULL	INPUT NULL	
6	REFERENCE	NC	
7	-Vs	INPUT NULL	
8	+V _S	REFERENCE	
9	Vout	-V _S	
10	SENSE	+V _S	
11	G = 1000	NC	
12	G = 100	Vout	
13	G = 10	SENSE	
14	OUTPUT NULL	G = 1000	
15	OUTPUT NULL	G = 100	
16	RG ₁	NC	
17		G = 10	
18		OUTPUT NULL	
19		OUTPUT NULL	
20		RG ₁	

NOTES:

- Case outline E, pins 11, 12, and 13; short to RG₂ for desired gain.
 Case outline 2, pins 14, 15, and 17; short to RG for desired gain.

FIGURE 1. Terminal connections.

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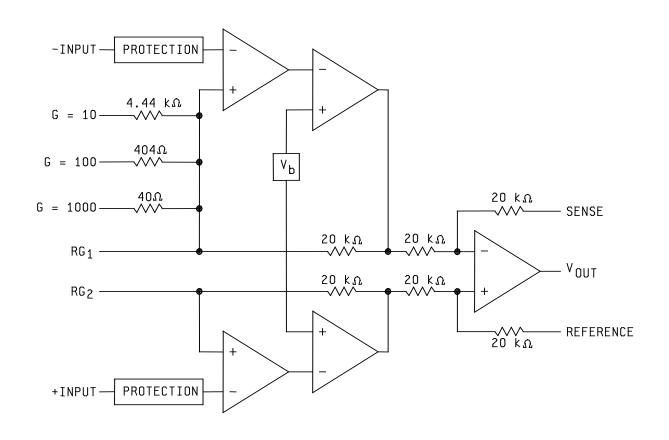


FIGURE 2. Block diagram.

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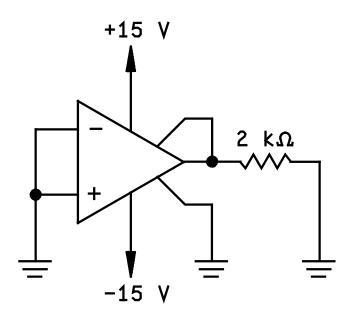


FIGURE 3. Radiation exposure circuit.

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4.2.1 Additional criteria for device class M.

- a. Burn-in test, method 1015 of MIL-STD-883.
 - (1) Test condition A, B, C, or D. The test circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing or acquiring activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in method 1015.
 - (2) $T_A = +125^{\circ}C$, minimum.
- b. Interim and final electrical test parameters shall be as specified in table IIA herein.

4.2.2 Additional criteria for device classes Q and V.

- a. The burn-in test duration, test condition and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-PRF-38535. The burn-in test circuit shall be maintained under document revision level control of the device manufacturer's Technology Review Board (TRB) in accordance with MIL-PRF-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in method 1015 of MIL-STD-883.
- b. Interim and final electrical test parameters shall be as specified in table IIA herein.
- Additional screening for device class V beyond the requirements of device class Q shall be as specified in MIL-PRF-38535, appendix B.
- 4.3 <u>Qualification inspection for device classes Q and V.</u> Qualification inspection for device classes Q and V shall be in accordance with MIL-PRF-38535. Inspections to be performed shall be those specified in MIL-PRF-38535 and herein for groups A, B, C, D, and E inspections (see 4.4.1 through 4.4.4).
- 4.4 <u>Conformance inspection</u>. Technology conformance inspection for classes Q and V shall be in accordance with MIL-PRF-38535 including groups A, B, C, D, and E inspections and as specified. Quality conformance inspection for device class M shall be in accordance with MIL-PRF-38535, appendix A and as specified herein. Inspections to be performed for device class M shall be those specified in method 5005 of MIL-STD-883 and herein for groups A, B, C, D, and E inspections (see 4.4.1 through 4.4.4).

4.4.1 Group A inspection.

- a. Tests shall be as specified in table IIA herein.
- b. Subgroups 4, 5, 6, 7, 8, 9, 10, and 11 in table I, method 5005 of MIL-STD-883 shall be omitted.
- 4.4.2 Group C inspection. The group C inspection end-point electrical parameters shall be as specified in table IIA herein.
- 4.4.2.1 Additional criteria for device class M. Steady-state life test conditions, method 1005 of MIL-STD-883:
 - a. Test condition A, B, C, or D. The test circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing or acquiring activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in method 1005 of MIL-STD-883.
 - b. $T_A = +125$ °C, minimum.
 - c. Test duration: 1,000 hours, except as permitted by method 1005 of MIL-STD-883.

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TABLE IIA. Electrical test requirements.

Test requirements	Subgroups	Subgr	oups
	(in accordance with	(in accordance with	
	MIL-STD-883,	MIL-PRF-385	35, table III)
	method 5005, table I)		T
	Device	Device	Device
	class M	class Q	class V
Interim electrical	1	1	1
parameters (see 4.2)			
Final electrical	1,2,3 <u>1</u> /	1,2,3 <u>1</u> /	1,2,3, <u>1</u> / <u>2</u> /
parameters (see 4.2)			
Group A test	1,2,3	1,2,3	1,2,3
requirements (see 4.4)			
Group C end-point electrical	1	1	1 <u>2</u> /
parameters (see 4.4)			
Group D end-point electrical	1	1	1
parameters (see 4.4)			
Group E end-point electrical			1
parameters (see 4.4)			

^{1/} PDA applies to subgroup 1.

TABLE IIB. 240 hour burn-in and group C end-point electrical parameters.

Parameter	Limit Delta		elta	
1 arameter	Min	Max	Min	Max
Voso		±3 mV		±3 mV

- 4.4.2.2 Additional criteria for device classes Q and V. The steady-state life test duration, test condition and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-PRF-38535. The test circuit shall be maintained under document revision level control by the device manufacturer's TRB in accordance with MIL-PRF-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in method 1005 of MIL-STD-883.
 - 4.4.3 <u>Group D inspection</u>. The group D inspection end-point electrical parameters shall be as specified in table IIA herein.
- 4.4.4 <u>Group E inspection</u>. Group E inspection is required only for parts intended to be marked as radiation hardness assured (see 3.5 herein).
 - a. End-point electrical parameters shall be as specified in table IIA herein.
 - b. For device classes Q and V, the devices or test vehicle shall be subjected to radiation hardness assured tests as specified in MIL-PRF-38535 for the RHA level being tested. For device class M, the devices shall be subjected to radiation hardness assured tests as specified in MIL-PRF-38535, appendix A for the RHA level being tested. All device classes must meet the postirradiation end-point electrical parameter limits as defined in table I at T_A = +25°C ±5°C, after exposure, to the subgroups specified in table IIA herein.

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^{2/} Delta limits as specified in table IIB shall be required where specified, and the delta limits shall be computed with reference to the previous interim electrical parameters.

4.4.4.1 <u>Total dose irradiation testing</u>. Total dose irradiation testing shall be performed in accordance with MIL-STD-883 method 1019, condition A and as specified herein.

PACKAGING

5.1 <u>Packaging requirements</u>. The requirements for packaging shall be in accordance with MIL-PRF-38535 for device classes Q and V or MIL-PRF-38535, appendix A for device class M.

6. NOTES

- 6.1 <u>Intended use</u>. Microcircuits conforming to this drawing are intended for use for Government microcircuit applications (original equipment), design applications, and logistics purposes.
- 6.1.1 <u>Replaceability</u>. Microcircuits covered by this drawing will replace the same generic device covered by a contractor-prepared specification or drawing.
- 6.2 <u>Configuration control of SMD's</u>. All proposed changes to existing SMD's will be coordinated with the users of record for the individual documents. This coordination will be accomplished using DD Form 1692, Engineering Change Proposal.
- 6.3 <u>Record of users</u>. Military and industrial users should inform DLA Land and Maritime when a system application requires configuration control and which SMD's are applicable to that system. DLA Land and Maritime will maintain a record of users and this list will be used for coordination and distribution of changes to the drawings. Users of drawings covering microelectronic devices (FSC 5962) should contact DLA Land and Maritime-VA, telephone (614) 692-0544.
- 6.4 <u>Comments</u>. Comments on this drawing should be directed to DLA Land and Maritime-VA, Columbus, Ohio 43218-3990, or telephone (614) 692-0540.
- 6.5 <u>Abbreviations, symbols, and definitions</u>. The abbreviations, symbols, and definitions used herein are defined in MIL-PRF-38535 and MIL-HDBK-1331.
 - 6.6 Sources of supply.
- 6.6.1 <u>Sources of supply for device classes Q and V</u>. Sources of supply for device classes Q and V are listed in QML-38535. The vendors listed in QML-38535 have submitted a certificate of compliance (see 3.6 herein) to DLA Land and Maritime-VA and have agreed to this drawing.
- 6.6.2 <u>Approved sources of supply for device class M.</u> Approved sources of supply for class M are listed in MIL-HDBK-103. The vendors listed in MIL-HDBK-103 have agreed to this drawing and a certificate of compliance (see 3.6 herein) has been submitted to and accepted by DLA Land and Maritime-VA.

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DATE: 11-02-16

Approved sources of supply for SMD 5962-88539 are listed below for immediate acquisition information only and shall be added to MIL-HDBK-103 and QML-38535 during the next revision. MIL-HDBK-103 and QML-38535 will be revised to include the addition or deletion of sources. The vendors listed below have agreed to this drawing and a certificate of compliance has been submitted to and accepted by DLA Land and Maritime -VA. This information bulletin is superseded by the next dated revision of MIL-HDBK-103 and QML-38535. DLA Land and Maritime maintains an online database of all current sources of supply at http://www.dscc.dla.mil/Programs/Smcr/.

Standard microcircuit drawing PIN <u>1</u> /	Vendor CAGE number	Vendor similar PIN <u>2</u> /	Reference military specification PIN
5962-8853901EA	24355 (2)	AD524SD/883B	M38510/14301BEX
5962-88539012A	<u>3</u> /	AD524SE/883B	
5962-8853901VEA	24355 (4)	AD524SD/QMLV	
5962-8853901V2A	24355 (4)	AD524SE/QMLV	
5962R8853901VEA	24355 (4)	AD524SD/QMLR	
5962R8853901V2A	24355 (4)	AD524SE/QMLR	

Vendor CAGEVendor namenumberand address

24355 Analog Devices (2)

RT 1 Industrial Park PO Box 9106 Norwood, MA 02062

Point of contact: 804 Woburn Street

Wilmington, MA 01887-3462

24355 Analog Devices (4)

RT 1 Industrial Park PO Box 9106 Norwood, MA 02062

Point of contact: 7910 Triad Center Drive

Greensboro, NC 27409-9605

The information contained herein is disseminated for convenience only and the Government assumes no liability whatsoever for any inaccuracies in the information bulletin.